L Number	Hits	Search Text	DB	Time stamp
-	42	The state of the s	USPAT	2004/08/09 07:44
_	12	"5587329"	USPAT	2004/08/09 08:57
_	34744	high\$1voltage low\$1voltage	USPAT;	2004/08/09 10:07
	31,11	113.141.010430 10.141.010430	US-PGPUB	2001/00/05 20:07
_	535	(high\$1voltage low\$1voltage) and	USPAT;	2004/08/09 08:58
	333	(silicon\$lon\$linsulat\$5)	US-PGPUB	2001,00,05 00.50
_	958	(high\$1voltage low\$1voltage) and (soi	USPAT;	2004/08/09 08:59
		silicon\$lon\$linsulat\$5)	US-PGPUB	2001,00,00
l _	.305	((high\$1voltage low\$1voltage) and (soi	USPAT:	2004/08/09 09:05
		silicon\$1on\$1insulat\$5)) and (thicker with	US-PGPUB	2001,00,05 05.05
		(device near region) (semiconductor near	00 10102	
		layer) (low\$1voltage near region))		
	3	(high\$1voltage near region) and	USPAT;	2004/08/09 10:11
		(low\$1voltage near region) and soi	US-PGPUB	2001,00,00 20121
l _	2		USPAT;	2004/08/09 10:32
	_	(low\$1voltage near device) and soi	US-PGPUB	1 2001, 00, 01 20102
l <u>.</u>	279		USPAT;	2004/08/09 11:37
1		2577 355 3523 .	US-PGPUB	2001,00,05 11.37
l <u> </u>	559	438/479.ccls. not (257/500.ccls.)	USPAT:	2004/08/09 12:47
	337	1 430/473.0018. NOC (237/300.0018.)	US-PGPUB	2004/00/05 12.47
_	80	438/295.ccls. not (438/479.ccls.	USPAT;	2004/08/09 12:59
-		257/500.ccls.)	US-PGPUB	2004/00/09 12:59
_	53	438/219.ccls. not (438/295.ccls.	USPAT;	2004/08/09 13:07
_	33	438/219.cc1s. not (438/295.cc1s.)	US-PGPUB	2004/00/09 13:0/
	140			2004/09/00 12:22
-	140	438/224.CCIS. NOC (438/219.CCIS.)	USPAT; US-PGPUB	2004/08/09 13:22
<u>_</u>	291	438/404.ccls. not (438/224.ccls.	USPAT;	2004/08/09 14:03
-	291	438/219.ccls. 438/295.ccls. 438/479.ccls.	US-PGPUB	2004/08/09 14:03
		257/500.ccls.)	US-PGPUB	
_	122	438/412.ccls. not (438/404.ccls.	USPAT;	2004/08/10 18:52
	123	438/224.ccls. 438/219.ccls. 438/295.ccls.	US-PGPUB	2004/08/10 18:52
		438/479.ccls. 257/500.ccls.)	US-PGPUB	
i _	1560	(silicon\$1on\$1insulator soi) and (nitride	USPAT;	2004/08/10 13:06
	1300	with oxide with remov\$5)	US-PGPUB	2004/08/10 13:06
_	216	• •	USPAT;	2004/08/10 15:26
	216	with oxide with remov\$5)) and (high adj	US-PGPUB	2004/08/10 15:26
		voltage\$1)	US-PGPUB	
_	1	"10367265"	JPO;	2004/08/10 15:12
	_	10307203	DERWENT	2004/08/10 13:12
_	1791	(silicon\$1on\$1insulator soi) and ((nitride	USPAT;	2004/08/10 15:37
	1751	with oxide) same thin\$5)	US-PGPUB	2004/08/10 13:37
_	992	1	USPAT;	2004/08/10 15:34
		with oxide) same thin\$5)) and ((nitride with	US-PGPUB	2001/00/10 13.31
		oxide) with thin\$5)	OB FGFOB	1
_	3022	l · · · · · · · · · · · · · · · · · · ·	USPAT;	2004/08/10 15:42
	3.1	with ((semiconductor near layer) (silicon	US-PGPUB	2001,00,10 13.12
		near layer) (high\$1voltage near (region		1
		area)) (low\$1voltage near (region area))))		
_	1486	((silicon\$1on\$1insulator soi) and (thin\$5	USPAT;	2004/08/10 15:45
		with ((semiconductor near layer) (silicon	US-PGPUB	-552, 50, 10 15.45
		near layer) (high\$1voltage near (region		
		area)) (low\$1voltage near (region area)))))	1	
		and (((remov\$5 etch\$5) oxide) with thin\$5		
		with ((semiconductor near layer) (silicon		
		near layer) (high\$1voltage near (region	1	
		area)) (low\$1voltage near (region area))))		
_	2498		USPAT;	2004/08/10 19:00
}	2170	(438/412.ccls. 438/404.ccls. 438/224.ccls.	US-PGPUB	2334,03,10 13.00
		438/219.ccls. 438/295.ccls. 438/479.ccls.	35 13102	
		257/500.ccls.)	İ	
_	253	((438/275.ccls. 257/347.ccls.) not	USPAT;	2004/08/10 19:01
		(438/412.ccls. 438/404.ccls. 438/224.ccls.	US-PGPUB	2301,00,10 13.01
		438/219.ccls. 438/295.ccls. 438/479.ccls.	== = ====	
		257/500.ccls.)) and (high adj voltage) and		
1		(low adj voltage)]
- 1	47	(((438/275.ccls. 257/347.ccls.) not	USPAT;	2004/08/10 19:01
l		(438/412.ccls. 438/404.ccls. 438/224.ccls.	US-PGPUB	= = = = = = = = = = = = = = = = = = =
]		438/219.ccls. 438/295.ccls. 438/479.ccls.		
ľ		257/500.ccls.)) and (high adj voltage) and		
l		(low adj voltage)) and (region near (thick\$5		
	ŀ	thin\$7))		
			L	I

-	1	"20040121547"	DERWENT	2004/08/10 19:11
-	4	(U11-C18A3 and U12-D02A3 and U12-D02A4 and	DERWENT	2004/08/10 19:11
		U12-Q).epi.		
-	1926	(L04-C07 and L04-C12).cpi.	DERWENT	2004/08/10 19:12
-	37	((L04-C07 and L04-C12).cpi.) and soi	DERWENT	2004/08/10 19:12
-	17	"5780900"	USPAT	2004/08/11 12:30
-	14	"5097314"	USPAT	2004/08/11 13:54
-	22	(silicon\$1on\$1insulator soi) and ((high adj	USPAT	2004/08/11 14:07
		voltage) near (area region section portion))		
		and ((low adj voltage) near (area region		
		section portion))		